

## Automotive-grade N-channel 60 V, 21 mΩ typ., 32 A STripFET™ F6 Power MOSFET in a PowerFLAT™ 5x6 package

Datasheet - production data

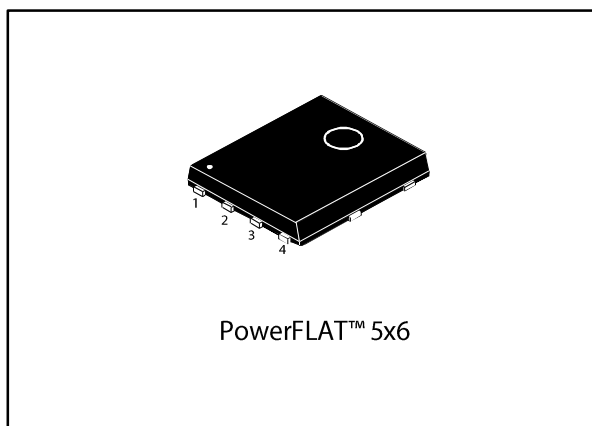


Figure 1: Internal schematic diagram

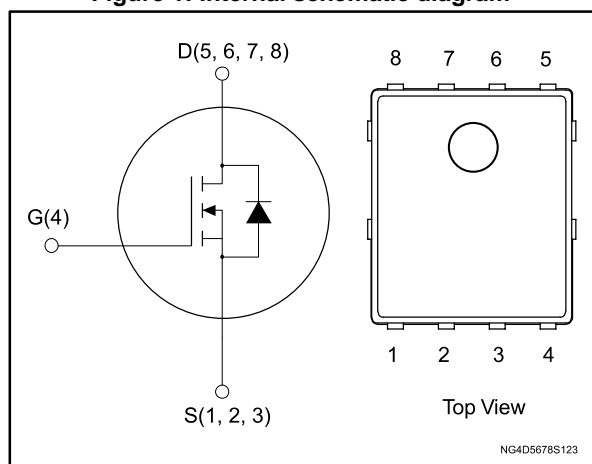


Table 1: Device summary

Order code	Marking	Package	Packing
STL8N6LF6AG	8N6LF6	PowerFLAT™ 5x6	Tape and reel

### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>	P <sub>TOT</sub>
STL8N6LF6AG	60 V	27 mΩ	32 A	55 W

- Designed for automotive applications and AEC-Q101 qualified
- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- Low gate drive power loss
- Wettable flank package

### Applications

- Switching applications

### Description

This device is an N-channel Power MOSFET developed using the STripFET™ F6 technology with a new trench gate structure. The resulting Power MOSFET exhibits very low R<sub>DS(on)</sub> in all packages.

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	60	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D$	Drain current (continuous) at $T_{case} = 25\text{ }^\circ\text{C}$	32	A
	Drain current (continuous) at $T_{case} = 100\text{ }^\circ\text{C}$	23	
$I_D^{(1)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	9.6	A
	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	6.8	
$I_{DM}^{(1)(2)}$	Drain current (pulsed)	38	A
$I_{DM}^{(2)}$	Drain current (pulsed)	128	A
$P_{TOT}$	Total dissipation at $T_{case} = 25\text{ }^\circ\text{C}$	55	W
$P_{TOT}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	4.8	
$T_{stg}$	Storage temperature	-55 to 175	$^\circ\text{C}$
$T_j$	Operating junction temperature		

**Notes:**

(1) When mounted on a 1-inch<sup>2</sup> FR-4, 2 Oz copper board,  $t < 10\text{ s}$ .

(2) Pulse width is limited by safe operating area.

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	2.7	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	31.3	

**Notes:**

(1) When mounted on a 1-inch<sup>2</sup> FR-4, 2 Oz copper board,  $t < 10\text{ s}$ .

**Table 4: Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AV}$	Avalanche current, not repetitive	32	A
$E_{AS}^{(1)}$	Single pulse avalanche energy	120	mJ

**Notes:**

(1) starting  $T_j = 25\text{ }^\circ\text{C}$ ,  $I_D = I_{AV}$ ,  $V_{DD} = 43.5\text{ V}$ .

## 2 Electrical characteristics

( $T_{\text{case}} = 25\text{ °C}$  unless otherwise specified)

**Table 5: Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	60			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 60\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	1		2.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 9.6\text{ A}$		21	27	m $\Omega$
		$V_{GS} = 4.5\text{ V}$ , $I_D = 9.6\text{ A}$		25	31	

**Table 6: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	1340	-	pF
$C_{oss}$	Output capacitance		-	90	-	
$C_{riss}$	Reverse transfer capacitance		-	60	-	
$Q_g$	Total gate charge	$V_{DD} = 30\text{ V}$ , $I_D = 9.6\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 14</a> : "Test circuit for gate charge behavior")	-	27	-	nC
$Q_{gs}$	Gate-source charge		-	4.6	-	
$Q_{gd}$	Gate-drain charge		-	4.3	-	

**Table 7: Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 30\text{ V}$ , $I_D = 12.5\text{ A}$ $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 13</a> : "Test circuit for resistive load switching times" and <a href="#">Figure 18</a> : "Switching time waveform")	-	9.6	-	ns
$t_r$	Rise time		-	20	-	
$t_{d(off)}$	Turn-off delay time		-	56	-	
$t_f$	Fall time		-	7	-	

**Table 8: Source-drain diode**

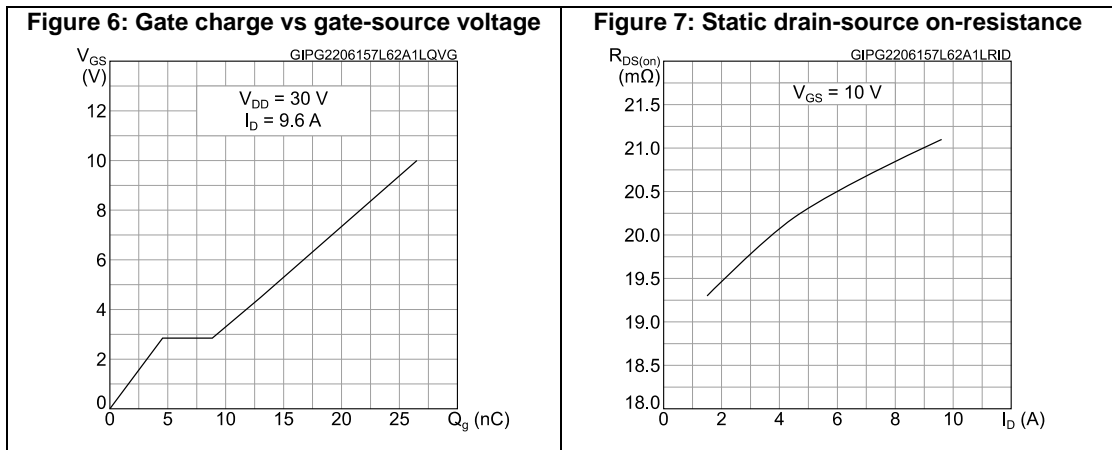
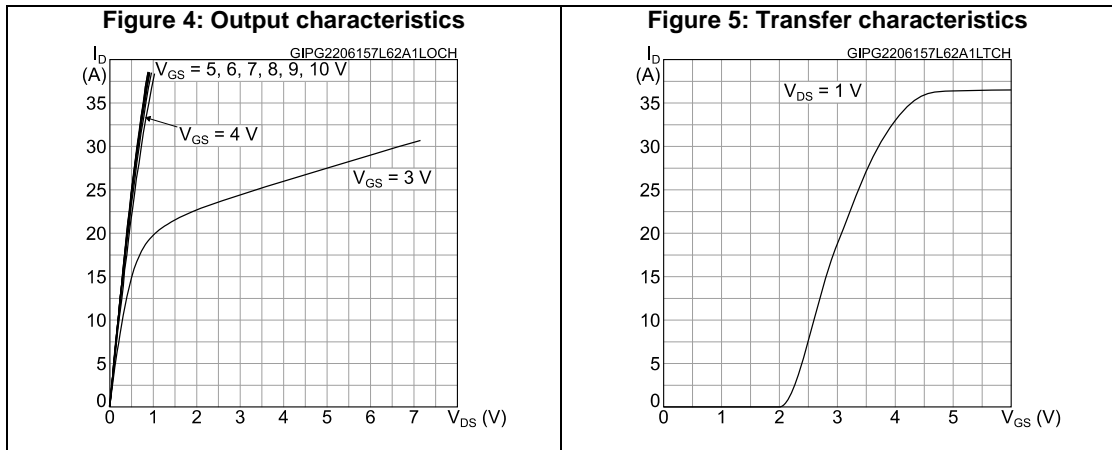
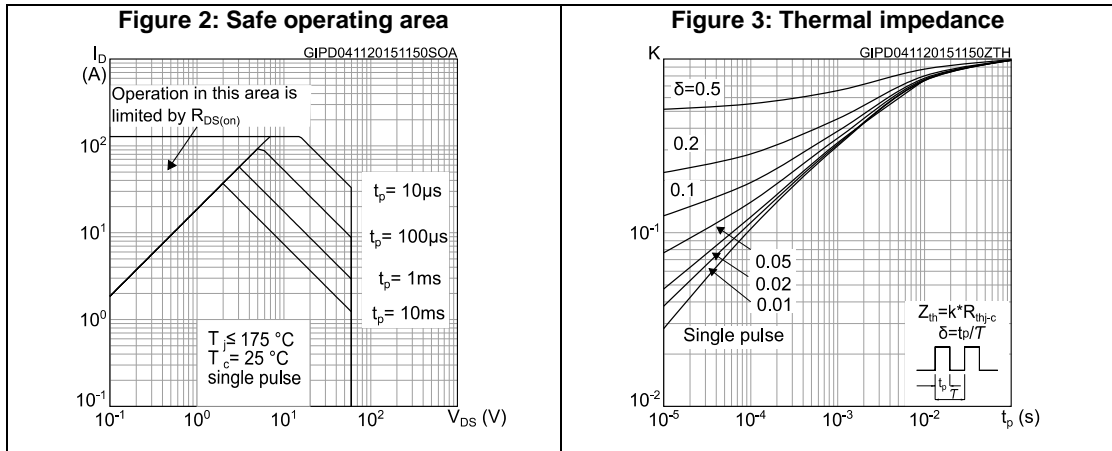
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		9.6	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		38	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$ , $I_{SD} = 9.6\text{ A}$	-		1.3	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 25\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 48\text{ V}$ (see <a href="#">Figure 15</a> : "Test circuit for inductive load switching and diode recovery times")	-	22.5		ns
$Q_{rr}$	Reverse recovery charge		-	22.2		nC
$I_{RRM}$	Reverse recovery current		-	2.0		A

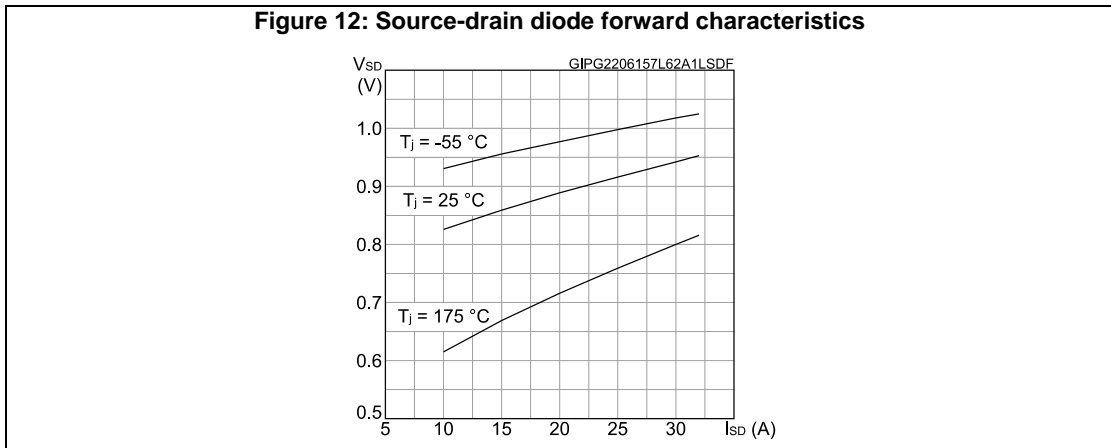
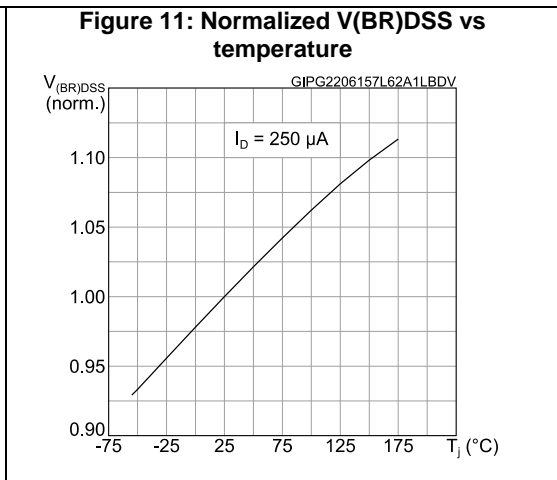
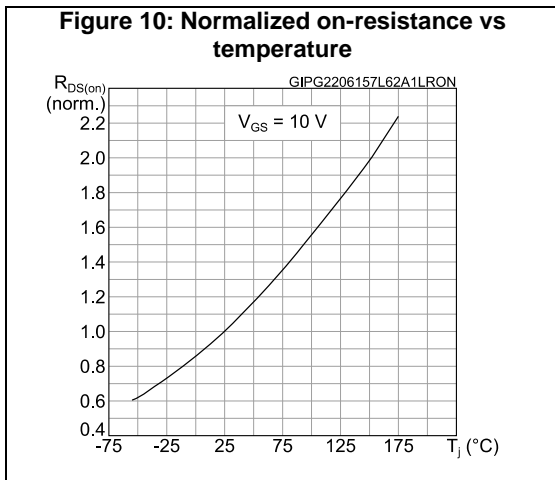
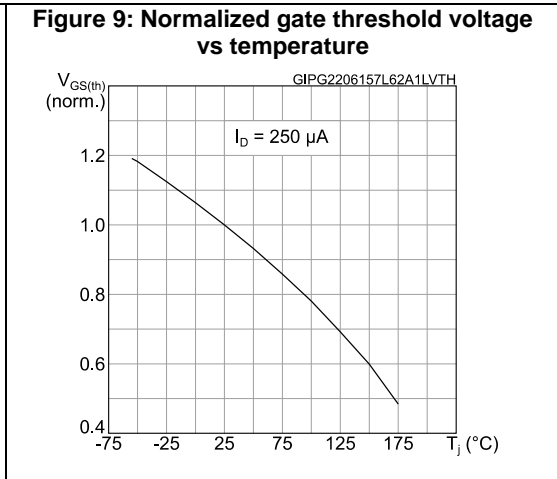
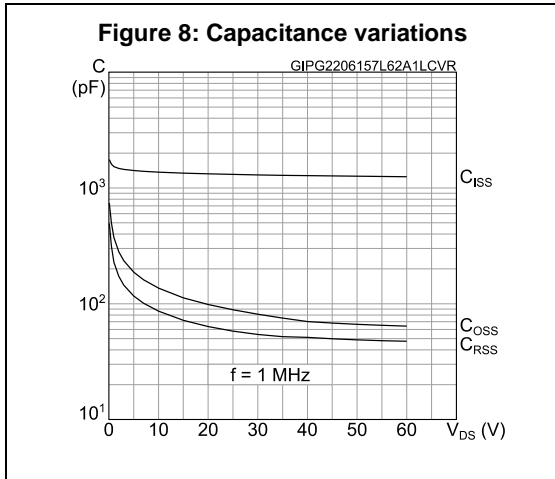
**Notes:**

(1) Pulse width is limited by safe operating area.

(2) Pulse test: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

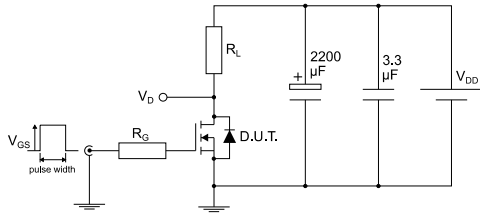
## 2.1 Electrical characteristics (curves)





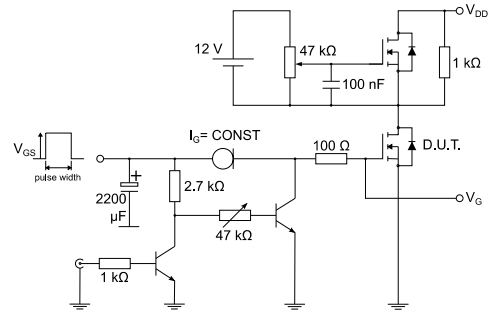
### 3 Test circuits

**Figure 13: Test circuit for resistive load switching times**



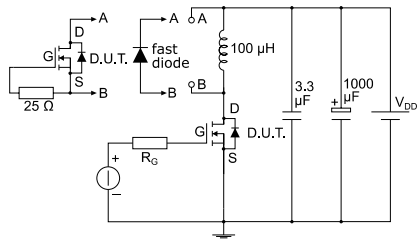
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**Figure 14: Test circuit for gate charge behavior**



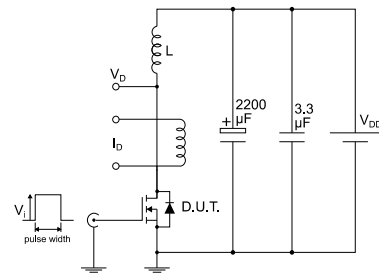
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**Figure 15: Test circuit for inductive load switching and diode recovery times**



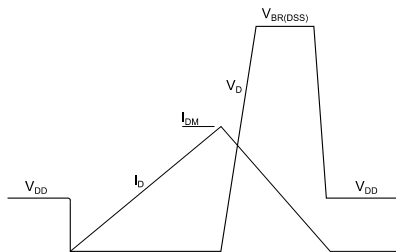
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**Figure 16: Unclamped inductive load test circuit**



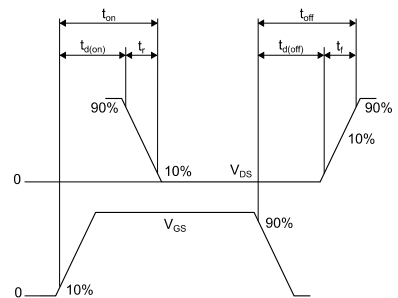
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**Figure 17: Unclamped inductive waveform**



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**Figure 18: Switching time waveform**



AM01473v1

# 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

## 4.1 PowerFLAT™ 5x6 WF type R package information

Figure 19: PowerFLAT™ 5x6 WF type R package outline

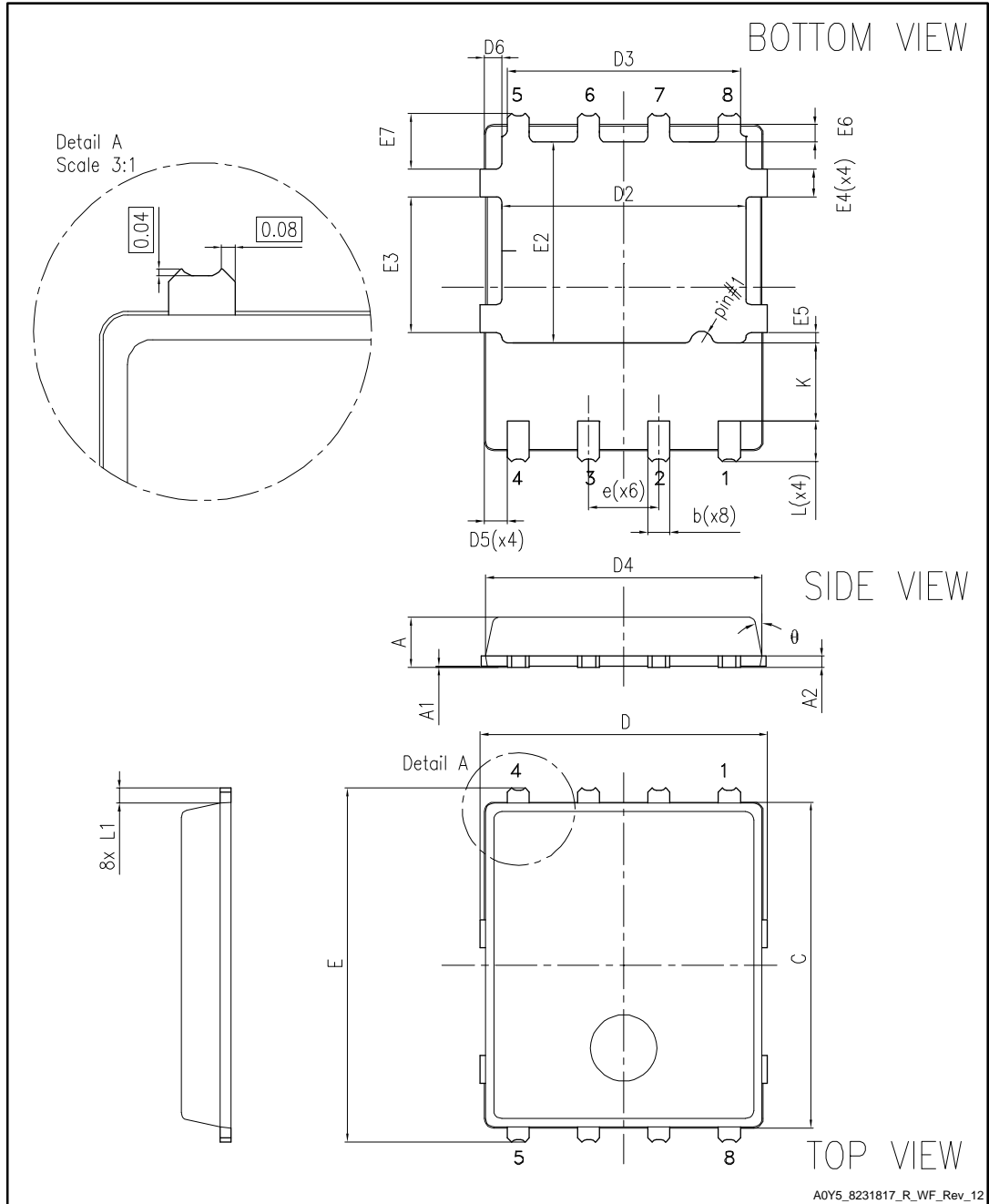
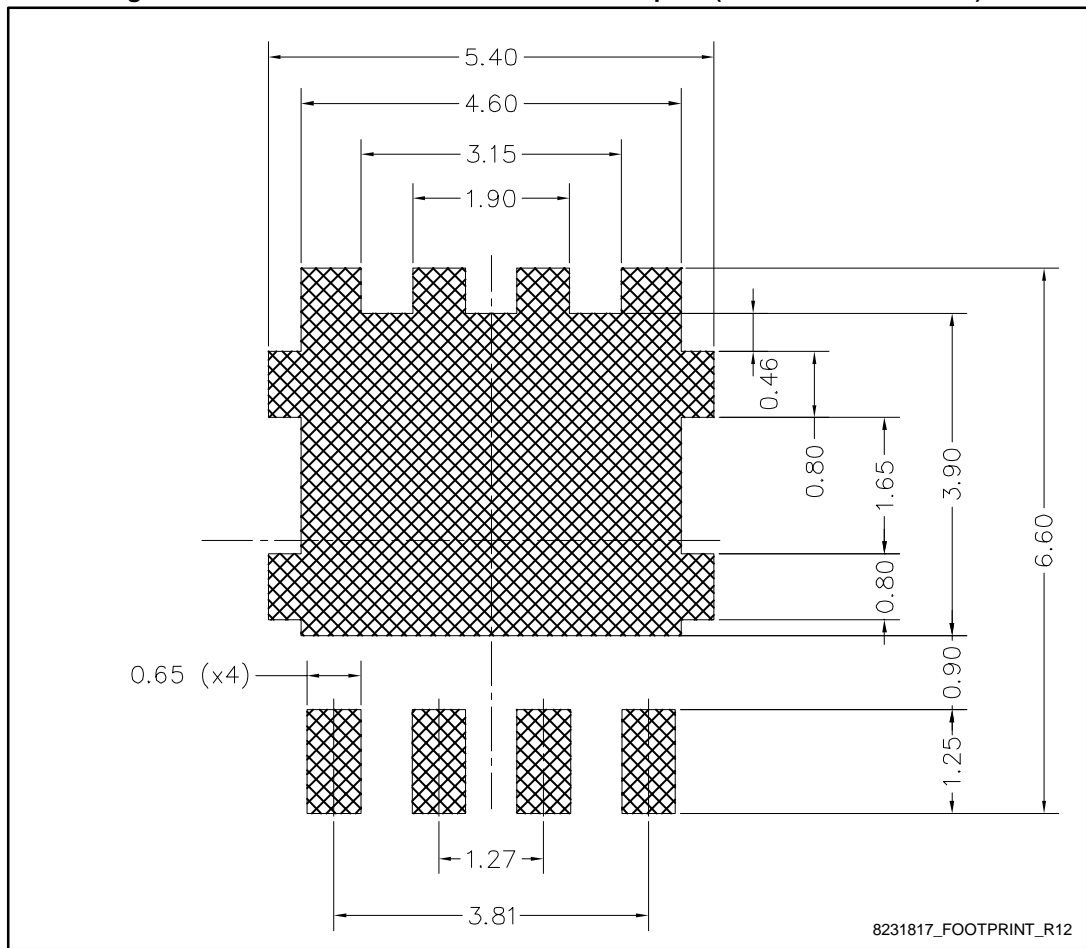




Table 9: PowerFLAT™ 5x6 WF type R mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
C	5.80	6.00	6.20
D	5.00	5.20	5.40
D2	4.15		4.45
D3	4.05	4.20	4.35
D4	4.80	5.0	5.20
D5	0.25	0.4	0.55
D6	0.15	0.3	0.45
e		1.27	
E	6.20	6.40	6.60
E2	3.50		3.70
E3	2.35		2.55
E4	0.40		0.60
E5	0.08		0.28
E6	0.175	0.325	0.450
E7	0.85	1.00	1.15
K	1.275		1.575
L	0.725	0.825	0.925
L1	0.175	0.275	0.375
Θ	0°		12°

Figure 20: PowerFLAT™ 5x6 recommended footprint (dimensions are in mm)



## 4.2 PowerFLAT™ 5x6 WF packing information

Figure 21: PowerFLAT™ 5x6 WF tape

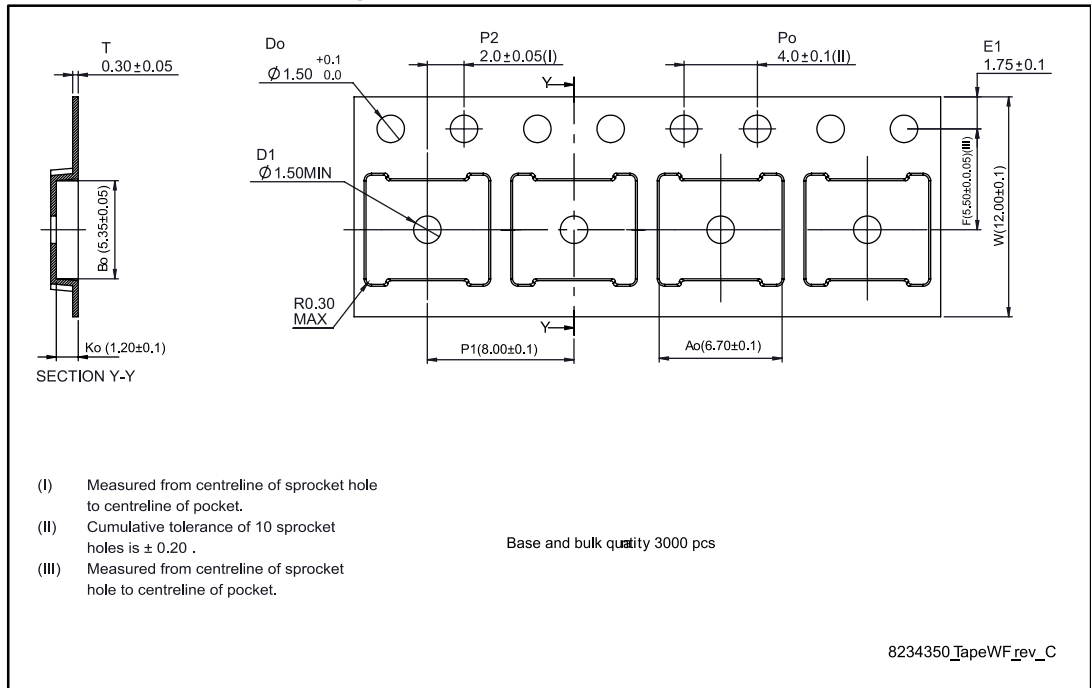


Figure 22: PowerFLAT™ 5x6 package orientation in carrier tape

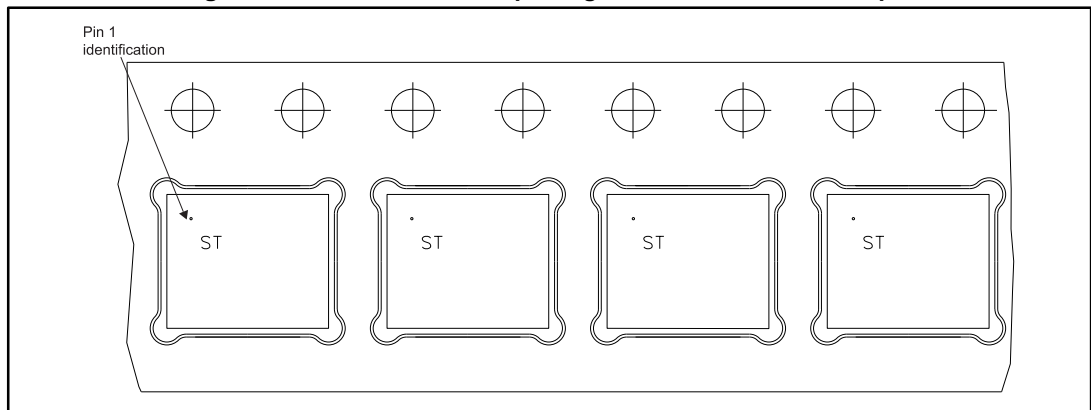
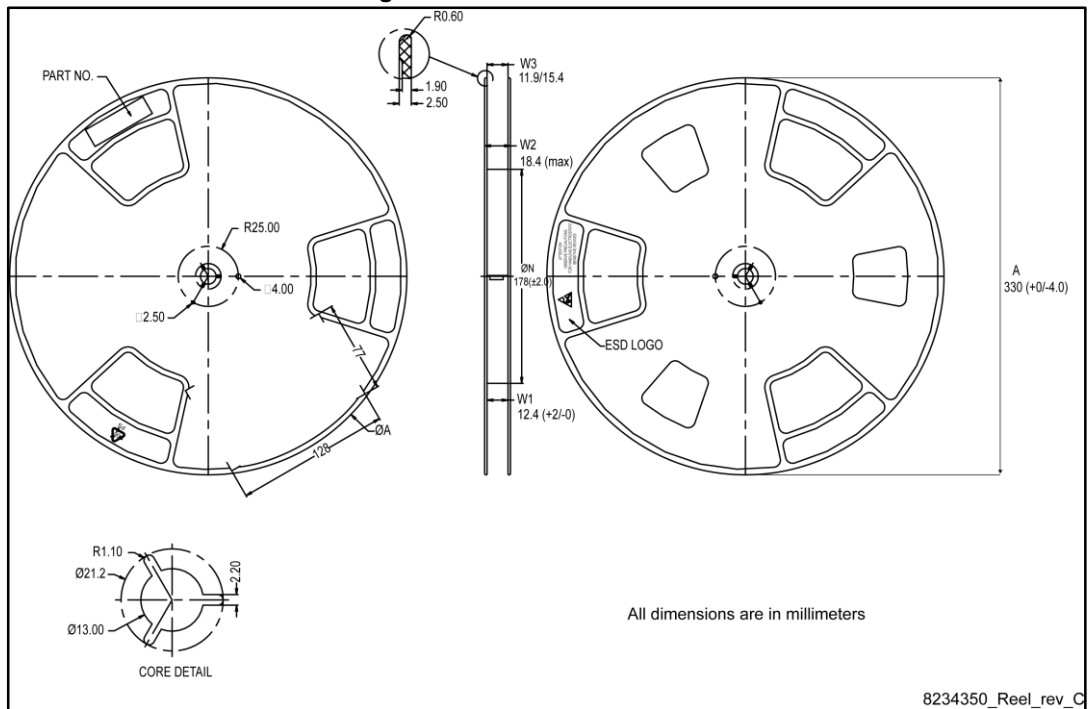


Figure 23: PowerFLAT™ 5x6 reel



## 5 Revision history

Table 10: Document revision history

Date	Revision	Changes
06-Jul-2015	1	First release.
07-Jan-2016	2	Updated title and features in cover page. Updated <i>Section 1: "Electrical ratings"</i> , <i>Section 2: "Electrical characteristics"</i> and <i>Section 4.1: "PowerFLAT™ 5x6 WF type R package information"</i> .

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